

Preferred Device

Switching Transistor

NPN Silicon

Features

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model; 4 kV, Machine Model; 400 V
- Pb–Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	40	Vdc
Collector-Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	600	mAdc

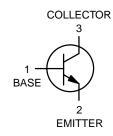
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board $T_A = 25^{\circ}C$	P _D	150	mW
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	833	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C



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SC-70 (SOT-323) CASE 419 STYLE 3

MARKING DIAGRAM



2X = Specific Device Code D = Date Code

ORDERING INFORMATION

Device		Package	Shipping [†]
MMBT4401W	T1	SC-70	3000/Tape & Reel
MMBT4401W	T1G	SC-70 (Pb-Free)	3000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

查诺尼尔尼的名字 经始合不合可任度 ISTU CS 商A = 25°C unless otherwise noted)

Charac	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (Note	V _{(BR)CEO}	40	-	Vdc	
Collector-Base Breakdown Voltage ($I_C = 0.1$	mAdc, $I_E = 0$)	V _{(BR)CBO}	60	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ r	nAdc, $I_C = 0$)	V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current ($V_{CE} = 35 \text{ Vdc}, V_{EB} = 0.$	I _{BEV}	_	0.1	μAdc	
ON CHARACTERISTICS (Note 1)					
$\label{eq:linear} \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 0.1 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 150 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 500 \text{ mAdc}, \text{V}_{CE} = 2.0 \text{ Vdc}) \end{array}$		h _{FE}	20 40 80 100 40	- - 300 -	_
Collector-Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$)	V _{CE(sat)}	-	0.4 0.75	Vdc	
Base-Emitter Saturation Voltage ($I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$)	V _{BE(sat)}	0.75	0.95 1.2	Vdc	
Collector Cutoff Current (V _{CE} = 35 Vdc, V _{EB}	= 0.4 Vdc)	I _{CEX}	-	0.1	μAdc
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product ($I_C = 20$	mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	f _T	250	-	MHz
Collector-Base Capacitance ($V_{CB} = 5.0$ Vdc	c, I _E = 0, f = 1.0 MHz)	C _{cb}	_	6.5	pF
Emitter–Base Capacitance ($V_{EB} = 0.5$ Vdc, I	_C = 0, f = 1.0 MHz)	C _{eb}	_	30	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE} = 10 V	h _{ie}	1.0	15	kΩ	
Voltage Feedback Ratio (I_C = 1.0 mAdc, V_{CE}	h _{re}	0.1	8.0	X 10 ⁻⁴	
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	40	500	-
Output Admittance (I _C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{oe}	1.0	30	μmhos
SWITCHING CHARACTERISTICS		1		•	
Delay Time	(V _{CC} = 30 Vdc, V _{EB} = 2.0 Vdc,	t _d	-	15	
Pise Time	$I_{\rm C} = 150 \text{ mAdc}$, $I_{\rm B1} = 15 \text{ mAdc}$)	t.	_	20	ns

Delay Time	$(V_{CC} = 30 \text{ Vdc}, V_{EB} = 2.0 \text{ Vdc},$	t _d	-	15	
Rise Time	$I_{C} = 150 \text{ mAdc}, I_{B1} = 15 \text{ mAdc})$	t _r	-	20	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$	t _s	-	225	
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$)	t _f	-	30	ns

1. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

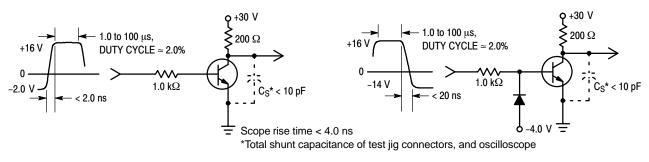
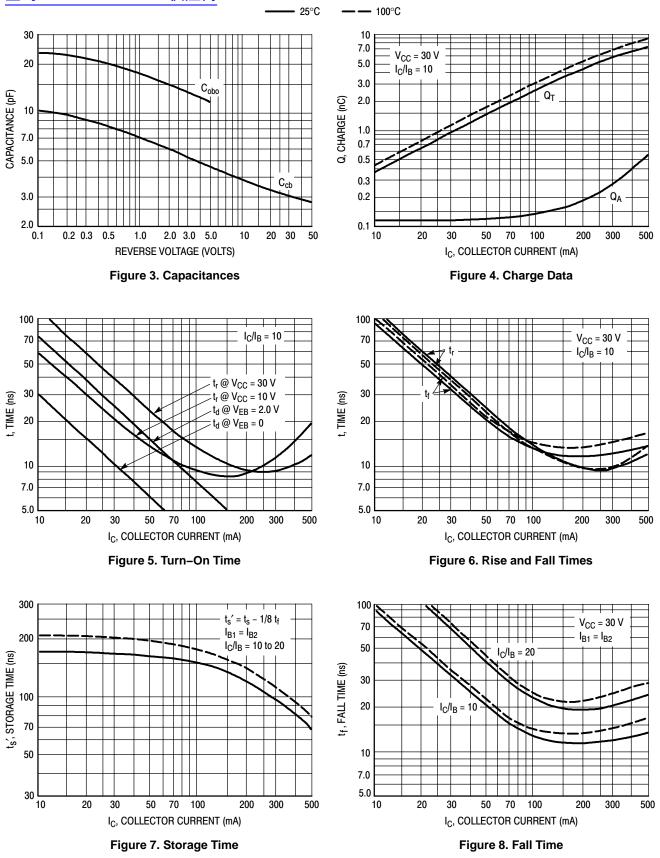


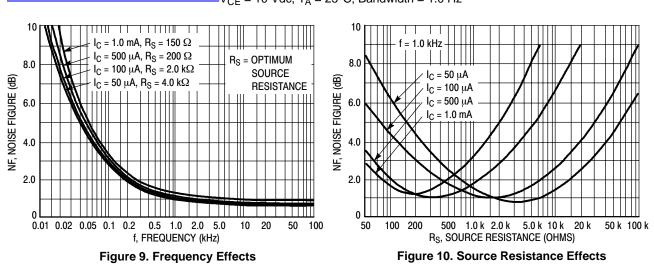
Figure 1. Turn-On Time

Figure 2. Turn–Off Time

查询"MMBT4401WT1G"供应商

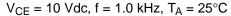
TRANSIENT CHARACTERISTICS



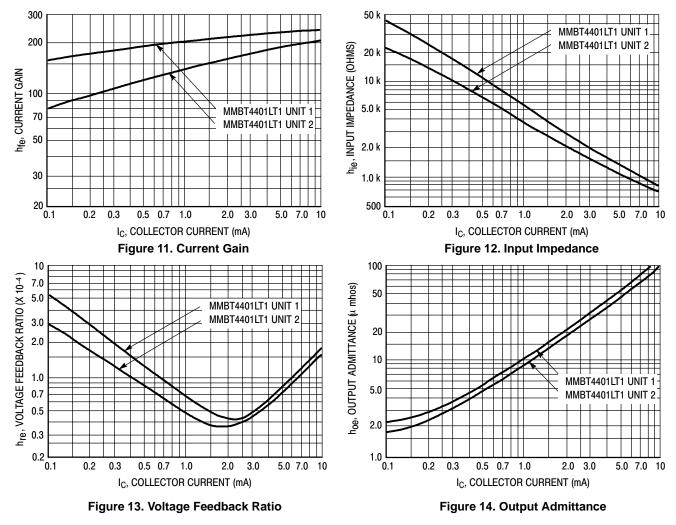


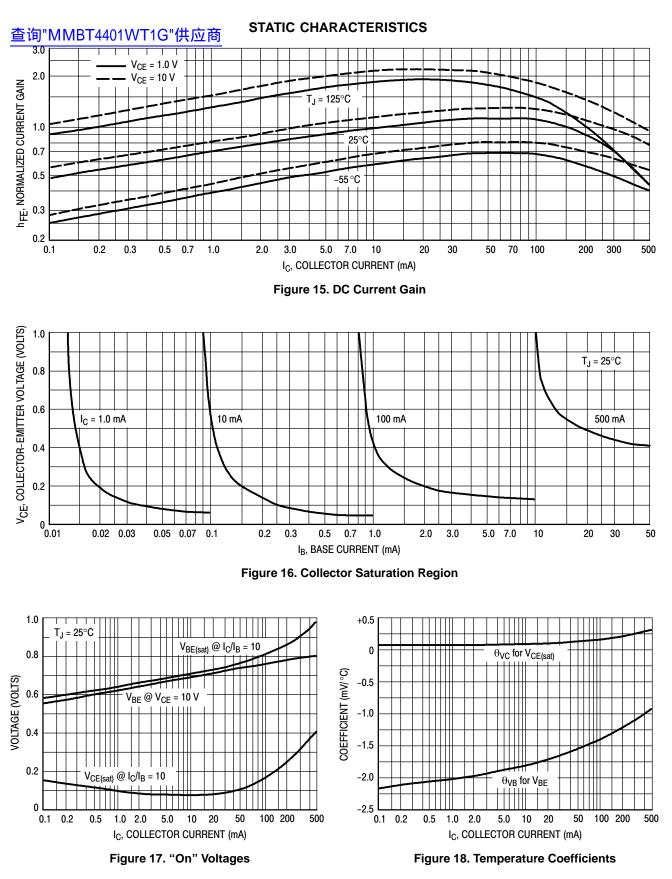
查询"MMBT4401WT1G"供应商_{VCE} = 10 Vdc, T_A = 25°C; Bandwidth = 1.0 Hz

h PARAMETERS



This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high–gain and a low–gain unit were selected from the MMBT4401WT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

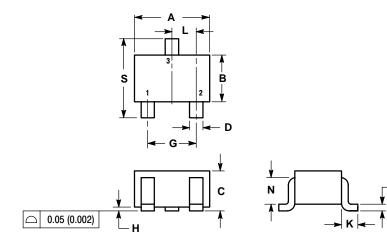




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PACKAGE DIMENSIONS

SC-70/SOT-323 CASE 419-04 ISSUE L



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI

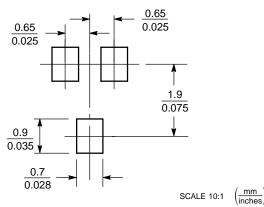
Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
С	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
Н	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
Κ	0.017 REF		0.425 REF	
L	0.026 BSC		0.650 BSC	
Ν	0.028 REF		0.700 REF	
S	0.079	0.095	2.00	2.40



2. EMITTER 3. COLLECTOR

SOLDERING FOOTPRINT*



SC-70/SOT-323

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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